

Appl. No. 09/895,524
Reply to Office action of 08/29/2003

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously amended): A method of fabricating an integrated circuit comprising the steps of:

forming a HDP (high density plasma) liner layer over a semiconductor body having metal leads formed thereon, wherein a portion of said HDP liner layer over said metal leads has sloped edges;

forming a gap-fill layer over said liner layer, said gap-fill layer filling a space between said metal leads;

forming a dielectric layer over said gap-fill layer and said metal leads; and

forming a via through said dielectric layer to at least one of metal leads.

Claim 2 (currently amended): The method of claim 1, wherein said sloped edges have a slope ~~on the order of~~ about 45°.

Claim 3 (original): The method of claim 1, wherein said dielectric layer comprises PETEOS.

Claim 4 (original): The method of claim 1, wherein said dielectric layer comprises a silane based oxide.

Claim 5 (previously amended) The method of claim 1, wherein the portion of HDP liner layer over the metal leads is triangular shaped.

Claim 6 (previously amended) The method of claim 1, wherein the portion of HDP liner layer over the metal leads is trapezoidal.

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Claim 7 (original): The method of claim 1, wherein said step of forming said HDP liner layer uses an etch-to-deposition ratio in the range of 0.18 to 0.40.

Claim 8 (original): The method of claim 1, wherein said HDP liner layer comprises undoped HDP silicon dioxide.

Claim 9 (original): The method of claim 1, wherein said HDP liner layer comprises fluorinated HDP oxide.

Claim 10 (original): The method of claim 1, wherein said HDP liner layer comprises phosphorous doped HDP oxide.

Claim 11 (original): The method of claim 1, wherein said gap-fill layer comprises a spin-on glass.

Claim 12 (original): The method of claim 1, wherein said gap-fill layer comprises HSQ.

Claims 13-18 (canceled).